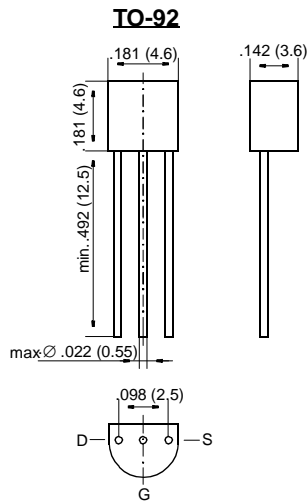


BS209

DMOS Transistors (P-Channel)



Dimensions in inches and (millimeters)

FEATURES

- ◆ High input impedance
- ◆ Low gate threshold voltage
- ◆ Low drain-source ON resistance
- ◆ High-speed switching
- ◆ No minority carrier storage time
- ◆ CMOS logic compatible input
- ◆ No thermal runaway
- ◆ No secondary breakdown



MECHANICAL DATA

Case: TO-92 Plastic Package

Weight: approx. 0.18 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

| | Symbol | Value | Unit |
|--|------------|-------------------|--------------------|
| Drain-Source Voltage | $-V_{DSS}$ | 400 | V |
| Drain-Gate Voltage | $-V_{DGS}$ | 400 | V |
| Gate-Source Voltage (pulsed) | V_{GS} | ± 20 | V |
| Drain Current (continuous) at $T_{amb} = 25\text{ }^{\circ}\text{C}$ | $-I_D$ | 120 | mA |
| Power Dissipation at $T_{amb} = 25\text{ }^{\circ}\text{C}$ | P_{tot} | 830 ¹⁾ | mW |
| Junction Temperature | T_j | 150 | $^{\circ}\text{C}$ |
| Storage Temperature Range | T_S | -65 to +150 | $^{\circ}\text{C}$ |

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

Inverse Diode

| | Symbol | Value | Unit |
|--|--------|-------|------|
| Max. Forward Current (continuous) at $T_{amb} = 25\text{ }^{\circ}\text{C}$ | I_F | 400 | mA |
| Forward Voltage Drop (typ.) at $V_{GS} = 0\text{ V}$, $I_F = 400\text{ mA}$, $T_j = 25\text{ }^{\circ}\text{C}$ | V_F | 1.0 | V |

BS209

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

| | Symbol | Min. | Typ. | Max. | Unit |
|--|-------------------------------------|-------------|-----------------|-------------------|----------------|
| Drain-Source Breakdown Voltage at $-I_D = 100 \mu\text{A}$, $V_{GS} = 0 \text{ V}$ | $-V_{(BR)DSS}$ | 400 | 430 | – | V |
| Gate-Body Leakage Current, Forward at $-V_{GSF} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$ | $-I_{GSSF}$ | – | – | 100 | nA |
| Gate-Body Leakage Current, Reverse at $-V_{GSR} = 20 \text{ V}$, $V_{DS} = 0 \text{ V}$ | $-I_{GSSR}$ | – | – | 100 | nA |
| Drain Cutoff Current at $-V_{DS} = 400 \text{ V}$, $V_{GS} = 0 \text{ V}$ | $-I_{DSS}$ | – | – | 500 | nA |
| Gate-Source Threshold Voltage at $V_{GS} = V_{DS}$, $-I_D = 250 \mu\text{A}$ | $-V_{GS(th)}$ | 1 | 1.5 | 2.5 | V |
| Drain-Source ON Resistance at $-V_{GS} = 5 \text{ V}$, $-I_D = 120 \text{ mA}$ | $R_{DS(on)}$ | – | 50 | 60 | Ω |
| Capacitance at $-V_{DS} = 25 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$ Input Capacitance Output Capacitance Feedback Capacitance | C_{iSS} C_{oSS} C_{rSS} | – – – | 200 30 10 | – – – | pF pF pF |
| Switching Times at $-V_{GS} = 10 \text{ V}$, $-V_{DS} = 10 \text{ V}$, $R_D = 100 \Omega$ Turn-On Time Turn-Off Time | t_{on} t_{off} | – – | 10 50 | – – | ns ns |
| Thermal Resistance Junction to Ambient Air | R_{thJA} | – | – | 150 ¹⁾ | K/W |

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.



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